## 2SK2426

## Silicon N-Channel MOS FET

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### Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC-DC converter.

## Outline





## 2SK2426

## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	12	А
Drain peak current	L <sub>D(pulse)</sub> *1	48	А
Body to drain diode reverse drain current	I <sub>DR</sub>	12	А
Channel dissipation	Pch*2	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW 10 µs, duty cycle 1 %

2. Value at Tc = 25 °C

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## **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	250	—	_	V	$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{\rm (BR)GSS}$	±30	—	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_		±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	—		250	μA	V <sub>DS</sub> =250 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	$V_{GS(off)}$	2.0		3.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$	—	0.23	0.35		I <sub>D</sub> = 6 A V <sub>GS</sub> = 10 V* <sup>1</sup>
Forward transfer admittance	y <sub>fs</sub>	5.0	8.0	—	S	I <sub>D</sub> = 6 A V <sub>DS</sub> = 10 V* <sup>1</sup>
Input capacitance	Ciss		1100	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss		440	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	68	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>		20	_	ns	I <sub>D</sub> = 6 A
Rise time	t,		65	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	100	_	ns	R <sub>L</sub> = 5
Fall time	t <sub>f</sub>	_	44	_	ns	
Body to drain diode forward voltage	$V_{DF}$		1.0	—	V	$I_F = 12 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	200	_	ns	$I_F = 12 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu \text{s}$
Note 1. Pulse Test						

Note 1. Pulse Test

See characteristics curves of 2SK1761, 2SK1762.

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